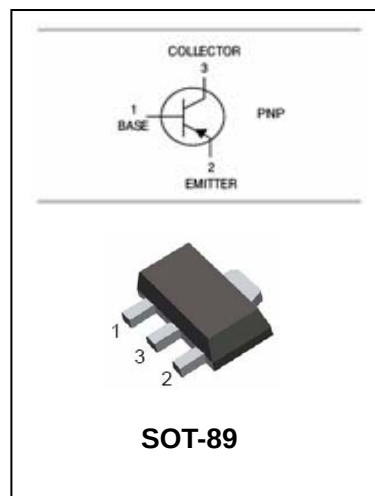


PNP EPITAXIAL PLANAR TRANSISTOR

HM4033

FEATURES

- The HM4033 is designed for high current general purpose amplifier applications.



ORDERING INFORMATION

Type No.	Marking	Package Code
HM4403	4403	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1	A
P_D	Power Dissipation	1.2	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C



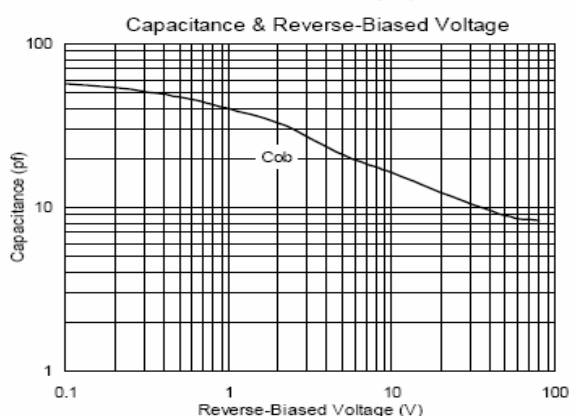
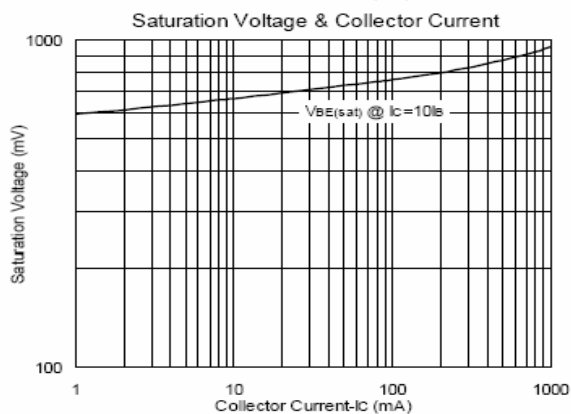
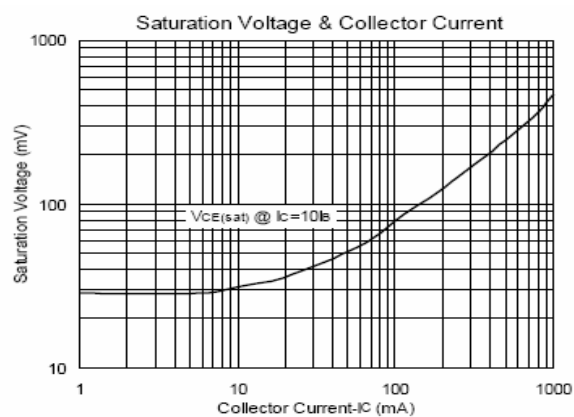
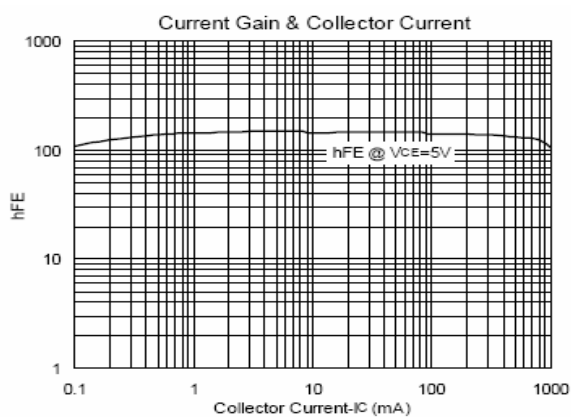
PNP EPITAXIAL PLANAR TRANSISTOR

HM4033

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-80		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V$		-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-100	nA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -0.1mA$	75		
		$V_{CE} = -5V, I_C = -0.1A$	100		
		$V_{CE} = -5V, I_C = -0.5A$	70		
		$V_{CE} = -5V, I_C = -1A$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150mA, I_B = -15mA$ $I_C = -500mA, I_B = -50mA$		-0.15 -0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150mA, I_B = -15mA$ $I_C = -500mA, I_B = -50mA$		-0.9 -1.1	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA,$ $f = 100MHz$	100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



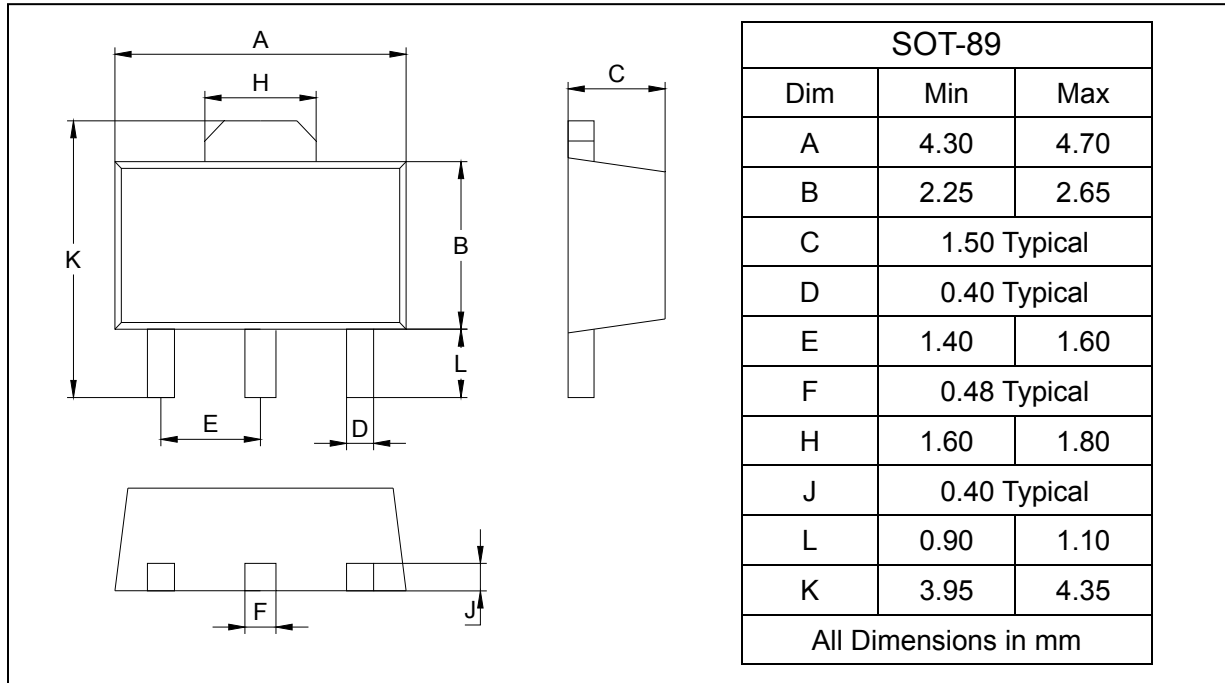
PNP EPITAXIAL PLANAR TRANSISTOR

HM4033

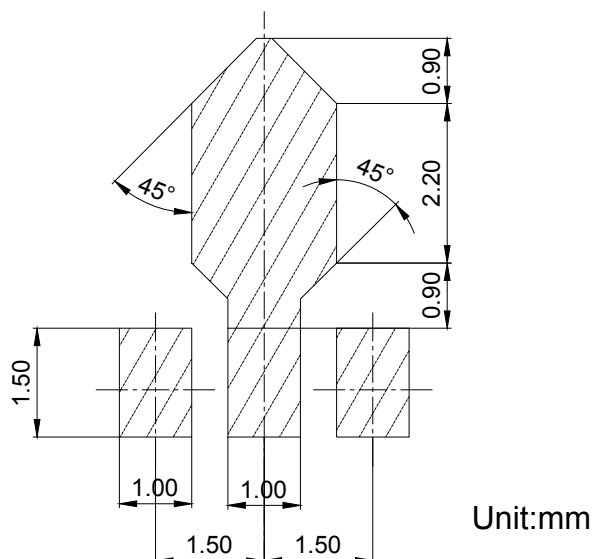
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
HM4033	SOT-89	1000/Tape&Reel